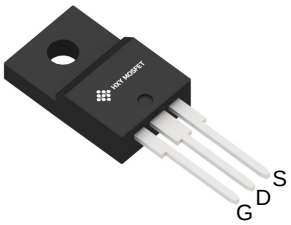
Description

The HXY20N50F can be used in various power swithching circuit for system miniaturization and higher efficiency.The package form is TO-220/ TO-220F, which accords with the RoHS standard.



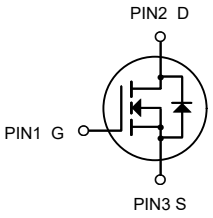
TO-220F

General Features

V_{DS} = 500V,I_D = 20A
$R_{DS(ON)}$ < 0.3Ω@ V_{GS}=10V

Application

● Power switch circuit of adaptor and charger.



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Units Tube
HXY20N50F	TO-220F	20N50 XXX YYYY	50

Absolute Maximum Ratings@T=25°C(unless otherwise specified)

Symbol	Parameter	Limit	Unit
V_{DSS}	Drain-to-Source Voltage[1]	500	V
V_{GSS}	Gate-to-Source Voltage	±30	
I_D	Continuous Drain Current	20	A
$I_{D\ @\ Tc=100°C}$	Continuous Drain Current @ Tc=100°C	Figure 3	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2]	Figure 6	
E_{AS}	Single Pulse Avalanche Energy	1500	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	165	W
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	°C
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 150	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.27	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Electrical Characteristics T_J =25 ° C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	500	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	V_{DS}=500V, V_{GS}=0V
		--	--	100		V_{DS}=400V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+30V, V_{DS}=0V
		--	--	-100		V_{GS}=-30V, V_{DS}=0V
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance[4]	--	0.26	0.3	Ω	V_{GS}=10V, I_D=10A
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250uA
gfs	Forward Transconductance[4]	--	17	--	S	VDS=15V,ID=10A
C_{iss}	Input Capacitance	--	2864	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MH_Z
C_{rss}	Reverse Transfer Capacitance	--	25	--		
C_{oss}	Output Capacitance	--	286	--		
Q_g	Total Gate Charge	--	63	--	nC	V_{DD}=250V, I_D=20A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	14	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	24	--		
$t_{d(ON)}$	Turn-on Delay Time	--	33	--	nS	V_{DD}=250V, I_D=20A, V_{GS}= 10V R_G=25 Ω
t_{rise}	Rise Time	--	75	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	181	--		
t_{fall}	Fall Time	--	83	--		
I_{SD}	Continuous Source Current[4]	--	--	20	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[4]	--	--	80		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	I_S=20A, V_{GS}=0V
trr	Reverse recovery time	--	392	--	V	V_{GS}=0V ,I_F=20A, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	3.3	--	uC	

Note:

[1] T_J=+25°C to +150°C
[2] Repetitive rating; pulse width limited by maximum junction temperature.
[3] I_{SD}= 20A di/dt < 100 A/μs, V_{DD} < BV_{DSS}, T_J=+150°C.
[4] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

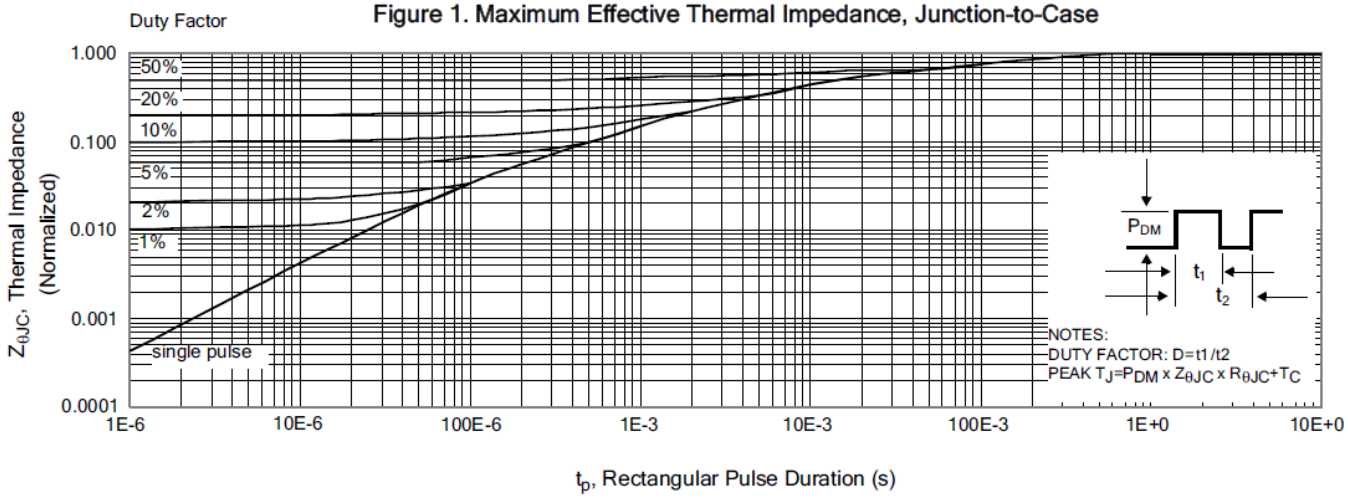


Figure 2. Maximum Power Dissipation vs Case Temperature

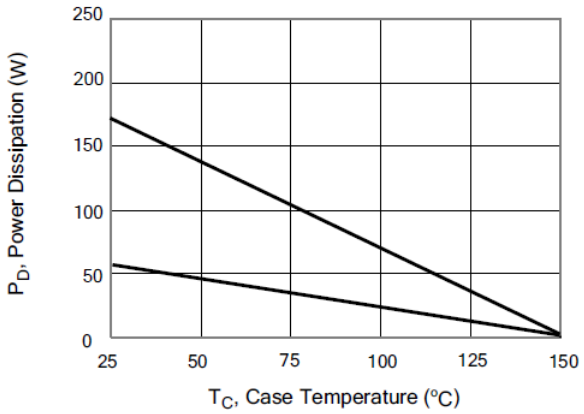


Figure 3. Maximum Continuous Drain Current vs Case Temperature

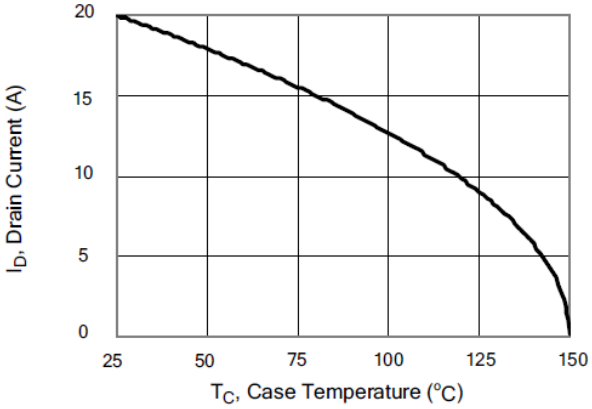


Figure 4. Typical Output Characteristics

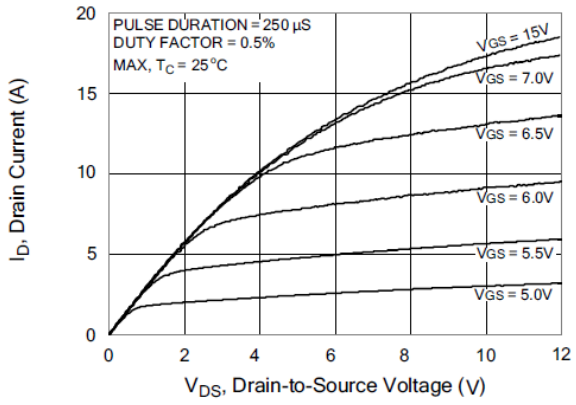


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

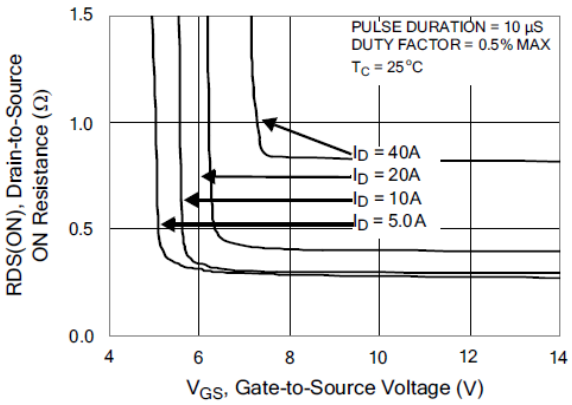


Figure 6. Maximum Peak Current Capability

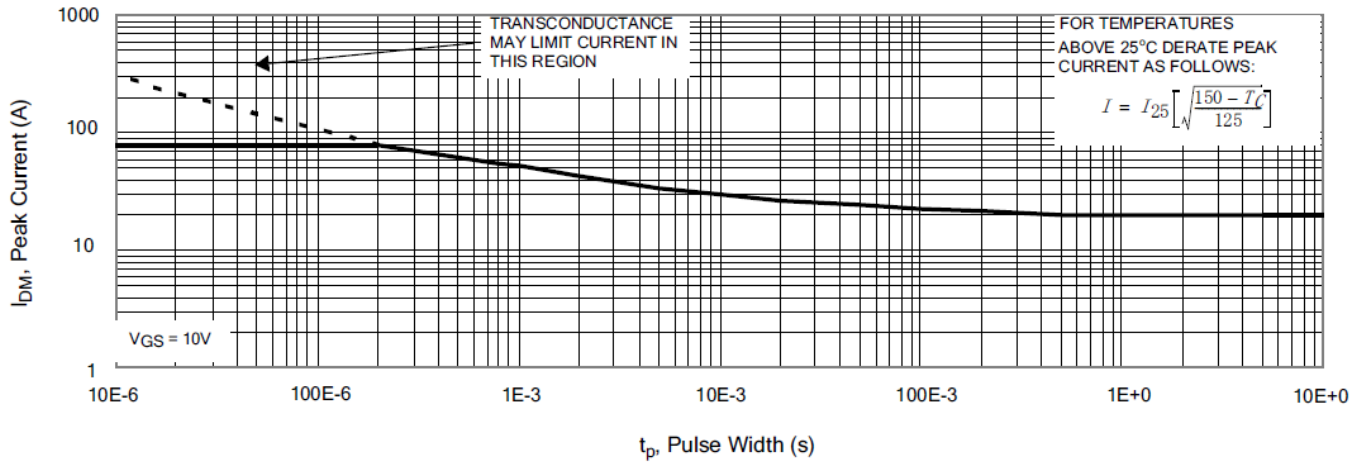


Figure 7. Typical Transfer Characteristics

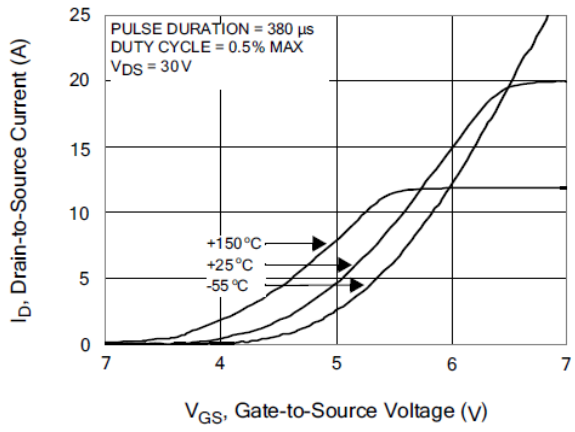


Figure 8. Unclamped Inductive Switching Capability

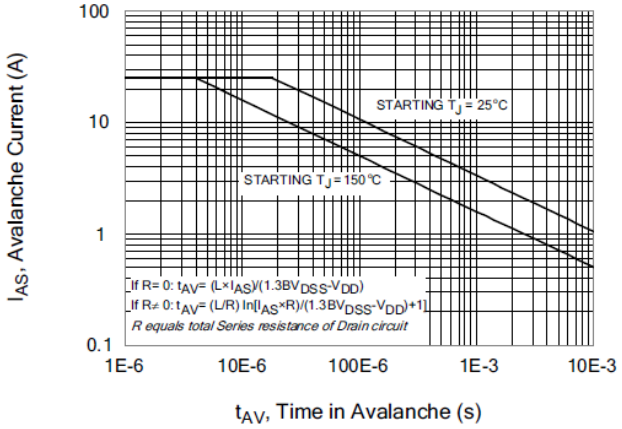


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

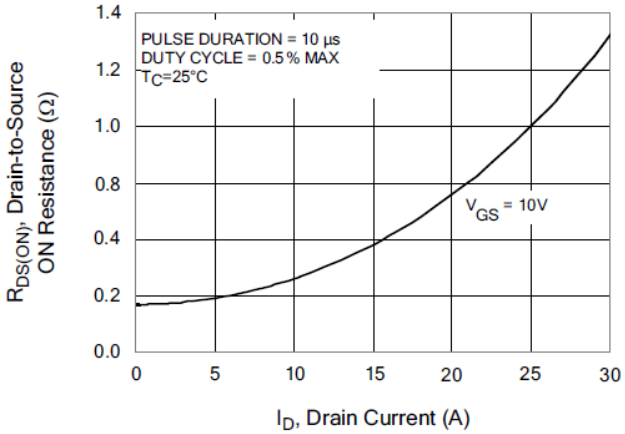


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

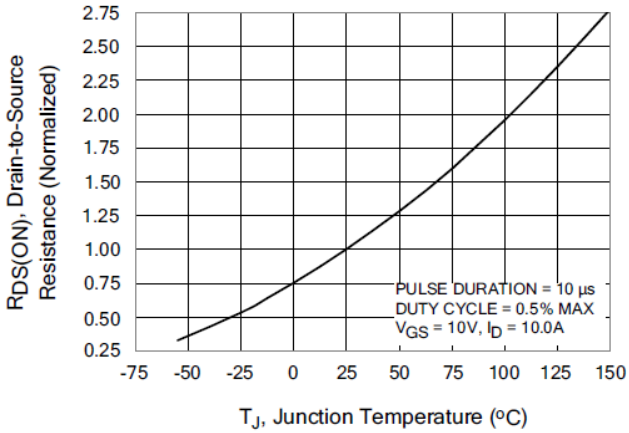


Figure 11. Typical Breakdown Voltage vs Junction Temperature

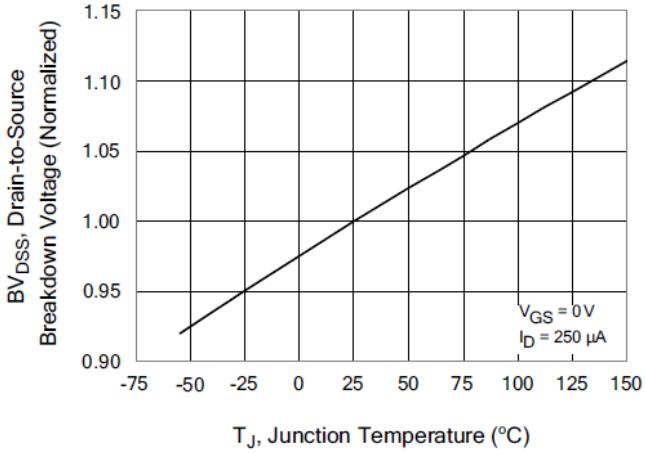


Figure 12. Typical Threshold Voltage vs Junction Temperature

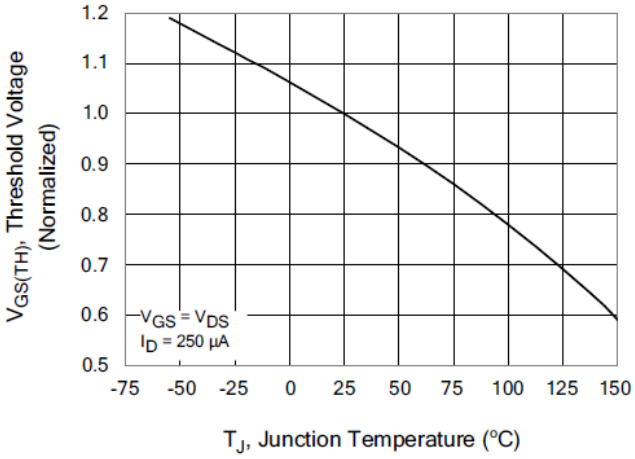


Figure 13. Maximum Forward Bias Safe Operating Area

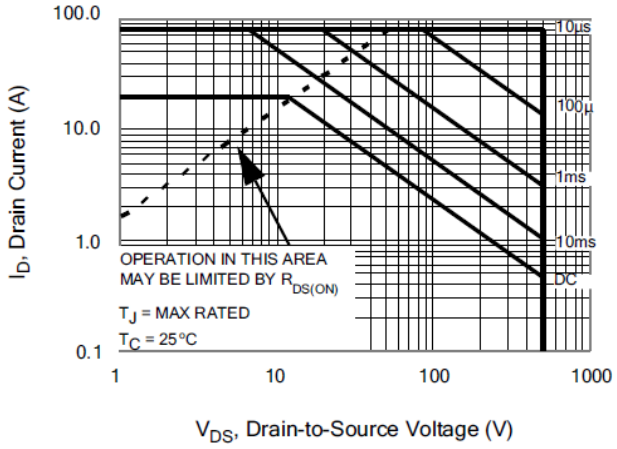


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

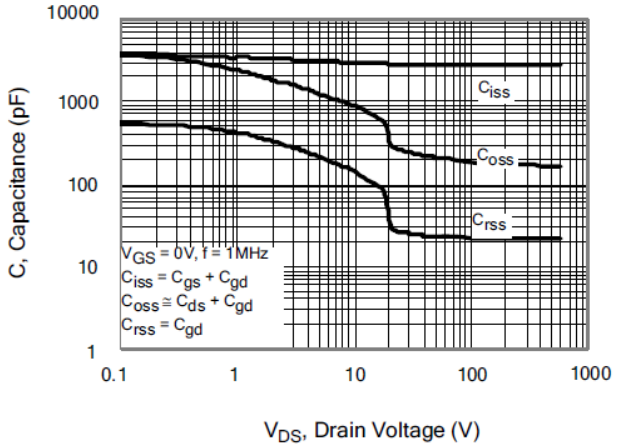


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

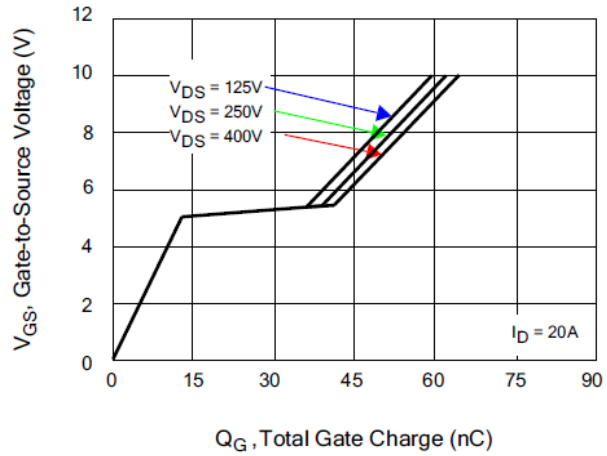
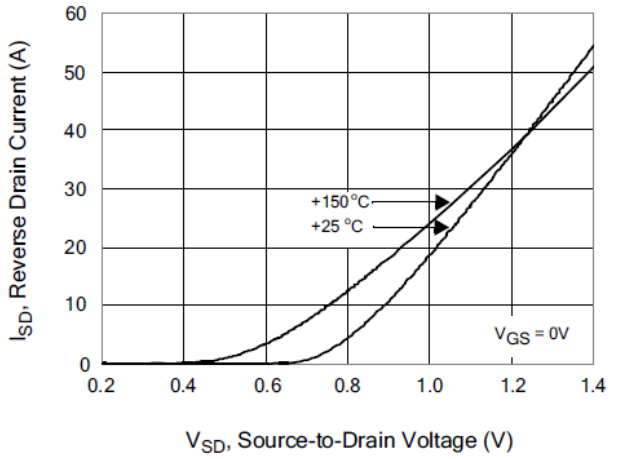
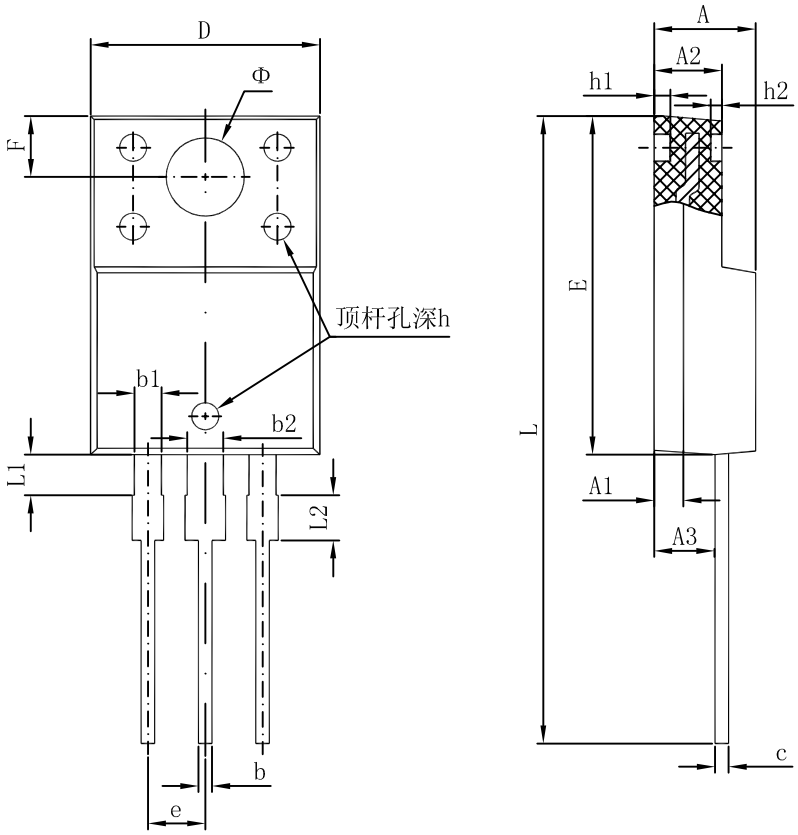


Figure 16. Typical Body Diode Transfer Characteristics



Package Dimension TO-220F



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	1.900	2.100	0.075	0.083

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